

Website update – ER presentation template

Marie-Curie Fellow

Name: Trapaidze

First Name: Lia

Age: 37

Nationality: Georgia

Position (ER/ESR): ER

Host institution: Department of Physics,

Aristotle University of Thessaloniki, Greece

Contract duration: 9 months



Short Education Background (10 lines max.)

- **10/2008 – 12/2008** Postdoc at the Japan Atomic Energy Agency (JAEA)
- **2002 Ph.D.** - Physics and Mathematics, Tbilisi, Georgia,
- **1998 - 2002**, Ph.D. student, Tbilisi State University, Tbilisi, Georgia
- **1995 -1997**, Public Administration College of TACIS: General Management, Information Systems and Technology, English Language Courses - Certificate (Tbilisi, Georgia)
- **1994 – 1995**, Faculty of Economic and Business Relation, Georgian Technical University, Manager, Diploma (Tbilisi, Georgia)
- **1989 – 1994**, Faculty of Applied Physics and General Technique, Georgian Technical University, Diploma of Master Degree (Tbilisi, Georgia)

Fellowships:

- **2006** - DAAD Fellowship, Erlangen-Nürnberg University, Germany,
- **2005** - NATO Research Fellowship, Gent University, Belgium,

Research focus and main activities carried out in the scope of the project (10 lines max.)

Microstructural characterization of the 3C-SiC layers grown on hexagonal SiC by TEM. The study will be focused on qualitative and quantitative investigation of different defects (i.e. micropipes, IDB, twins, stacking faults and dislocations) and their evolution during growth.

Publications (please specify when the publication has been issued in the scope of the MANSiC project)

1. M. Krieger, S. Beljakowa, L. Trapaidze, T. Frank, H. B. Weber, G. Pensl, N. Hatta, M. Abe, H. Nagasawa, A. Schöner, "Analysis of interface trap parameters from double-peak conductance spectra taken on N-implanted 3C-SiC MOS capacitors", *Silicon Carbide*, Vol. 1, (2010) pp. 363-374
2. M. Weidner, L. Trapaidze, G. Pensl, S. A. Reshanov, A. Schöner, H. Itoh, T. Ohshima and T. Kimoto, "Deep Defects in 3C-SiC Generated by H⁺- and He⁺-implantation or by Irradiation with High-energy Electrons", *Materials Science Forum* Vols. 645-648 (2010) pp. 439-442
3. Y. Nanen, B. Zippelius, S. Beljakowa, L. Trapaidze, M. Krieger, T. Kimoto, G. Pensl, "Preannealing Effect on Mobility of N-/Al-Coimplanted and Over-Oxidized 4H-SiC MOSFETs", *Materials Science Forum* Vols. 645-648 (2010) pp. 487-490
4. S. Beljakowa, M. Krieger, T. Frank, G. Pensl, L. Trapaidze, N. Hatta, M. Abe, H. Nagasawa, A. Schöner, "Two Different Species of Traps Monitored at N-implanted 3C-SiC MOS Capacitors by Conductance Spectroscopy", *Materials Science Forum* 600-603 (2009), p. 727
5. M. Krieger, S. Beljakowa, L. Trapaidze, T. Frank, H. B. Weber, G. Pensl, N. Hatta, M. Abe, H. Nagasawa, A. Schöner, "Analysis of interface trap parameters from double-peak conductance spectra taken on N-implanted 3C-SiC MOS capacitors", *Phys. Stat. Sol (b)*, 245 (2008), # 7, pp. 1390-1395